



PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes Examiner: Joannie A. Garcia
Serial No.: 10/634,174 Group Art Unit: 2823
Filed: August 05, 2003 Docket: 1303.102US1
Title: STRAINED Si/SiGe/SOI ISLANDS AND PROCESSES OF MAKING SAME

INFORMATION DISCLOSURE STATEMENT

MS RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. § 1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement. However, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Information Disclosure Statement considered.

Pursuant to 37 C.F.R. 1.98(a)(2), Applicant believes that copies of cited U.S. Patents and Published Applications are no longer required to be provided to the Office. Notification of this change was provided in the United States Patent and Trademark Office OG Notices dated October 12, 2004. Thus, Applicant has not included copies of any US Patents or Published Applications cited with this submission. Should the Office require copies to be provided, Applicant respectfully requests that notice of such requirement be directed to Applicant's below-signed representative. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

LEONARD FORBES

By his Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 373-6960

Date 7-19-06

By Marvin L. Beekman
Marvin L. Beekman
Reg. No. 38,377

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Mail Stop RCE, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 19 day of July 2006.

Lisa Rosecrace
Name

Susan Rosecrace
Signature

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(use as many sheets as necessary)</small>		<small>Complete if Known</small>	
		Application Number 10/634,174 Filing Date August 5, 2003 First Named Inventor Forbes, Leonard Group Art Unit 2823 Examiner Name Garcia, Joannie	
<small>Sheet 1 of 2</small>		Attorney Docket No: 1303.102US1	

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Filing Date If Appropriate
	US-20020185686A1	12/12/2002	Christiansen, S. H., et al.	04/03/2002
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	JP-04-304653	10/28/1992	ARIMOTO, Y. , et al.	English Abstract only

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Non-Final Office Action dated February 10, 2006, <u>U.S. Application Serial No. 10/979,994</u> , filed November 3, 2004, 20 pgs.	
		ANG, KAH W., "Enhanced performance in 50 nm N-MOSFETs with silicon-carbon source/drain regions", <u>IEEE International Electron Devices Meeting, 2004. IEDM Technical Digest</u> , (Dec., 2004),1069-1071	
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EXAMINER

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		Application Number	10/634,174
		Filing Date	August 5, 2003
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2823
		Examiner Name	Garcia, Joannie
Sheet 2 of 2		Attorney Docket No: 1303.102US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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